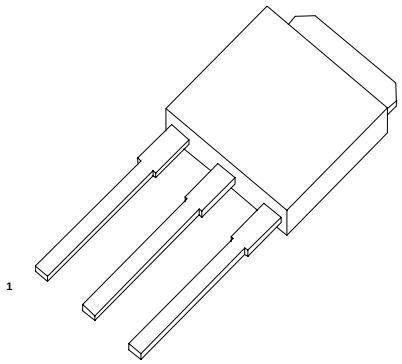
MX516
PNP Epitaxial Silicon Transistor

AUDIO FREQUENCY POWER AMPLIFIER
LOW SPEED SWITCHING
HIGH CURRENT HIGH POWER

- Complimentary to MX506

TO - 251



1. Base 2.Collector 3.Emitter

Absolute Maximum Ratings (TA=25°C

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-5	A
Collector Dissipation	P_C	5	W
Junction Temperature	T_J	150	°C

Electrical Characteristics (TA=25°C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C= -100μA, I_E=0	-30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C= -10mA, I_B=0	-20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E= -100μA, I_C=0	-6			V
Collector Cutoff Current	I_{CBO}	V_{CB}= -20V, I_C=0			-0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{BE}= -6V, I_C=0			-0.1	μA
Leakage Current	I_{CEO}	V_{CE}= -10V, I_C=0			-10	μA
DC Current Gain	h_{FE}	V_{CE}= -1V, I_C= -500mA	140		600	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C= -3A, I_B= -75mA			-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	V_{CE}= -1V, I_C= -3A			-1.5	V

h_{FE} CLASSIFICATION

Classification	Y	GR	BL
h_{FE}	140 – 280	200 – 400	300 – 600

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